

Sonic Fast Recovery Diode

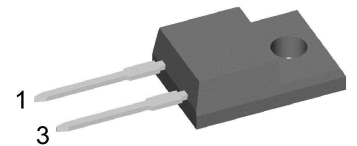
preliminary

V_{RRM}	=	1200 V
I_{FAV}	=	10 A
t_{rr}	=	75 ns


High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

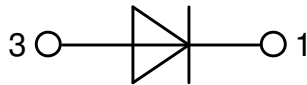
Part number

DHG10I1200PM



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

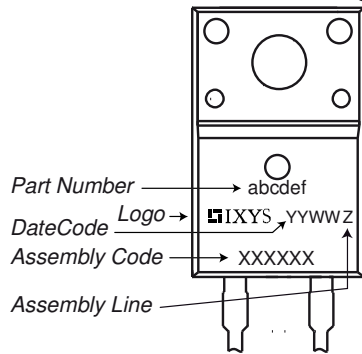
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V	
I_R	reverse current, drain current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		15	μA	
		$V_R = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$		1.2	mA	
V_F	forward voltage drop	$I_F = 10\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		2.22	V	
		$I_F = 20\text{ A}$			2.92	V	
		$I_F = 10\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$		2.13	V	
		$I_F = 20\text{ A}$			3.06	V	
I_{FAV}	average forward current	$T_C = 30^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}\text{C}$		10	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$		1.09	V	
r_F	slope resistance				94	m Ω	
R_{thJC}	thermal resistance junction to case				4	K/W	
R_{thCH}	thermal resistance case to heatsink			0.50		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$		30	W	
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$		65	A	
C_J	junction capacitance	$V_R = 600\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		4	pF	
I_{RM}	max. reverse recovery current	} $I_F = 10\text{ A}; V_R = 800\text{ V}$ $-di_F/dt = 350\text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		8	A	
			$T_{VJ} = \text{ }^{\circ}\text{C}$		tbd	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}\text{C}$		75	ns	
			$T_{VJ} = \text{ }^{\circ}\text{C}$		tbd	ns	

Package TO-220FP				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			35	A	
T_{VJ}	virtual junction temperature		-55		150	°C	
T_{op}	operation temperature		-55		125	°C	
T_{stg}	storage temperature		-55		150	°C	
Weight				2		g	
M_D	mounting torque		0.4		0.6	Nm	
F_C	mounting force with clip		20		60	N	
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	3.2	2.7		mm	
$d_{Spb/Apb}$		terminal to backside	2.5	2.5		mm	
V_{ISOL}	isolation voltage	t = 1 second	2500			V	
		t = 1 minute	2100			V	

Product Marking



Part description

- D = Diode
- H = Sonic Fast Recovery Diode
- G = extreme fast
- 10 = Current Rating [A]
- I = Single Diode
- 1200 = Reverse Voltage [V]
- PM = TO-220ACFP (2)

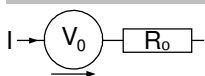
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG10I1200PM	DHG10I1200PM	Tube	50	503672

Similar Part	Package	Voltage class
DHG10I1200PA	TO-220AC (2)	1200

Equivalent Circuits for Simulation

* on die level

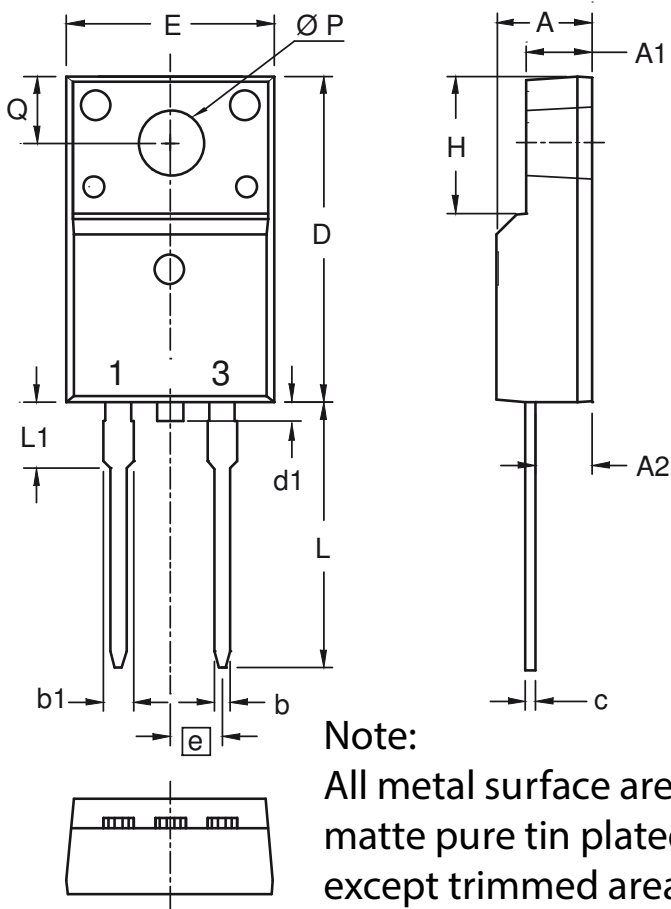
$T_{VJ} = 150\text{ °C}$



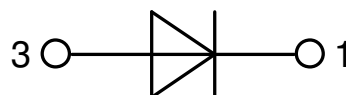
Fast Diode

$V_{0\ max}$	threshold voltage	1.09	V
$R_{0\ max}$	slope resistance *	91	mΩ

Outlines TO-220FP



Dim.	Millimeters		Inches	
	min	max	min	max
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
b1	1.27	1.47	0.050	0.058
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
d1	0	1.10	0	0.043
E	9.96	10.36	0.392	0.408
e	2.54 BSC		0.100 BSC	
H	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
ØP	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



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